

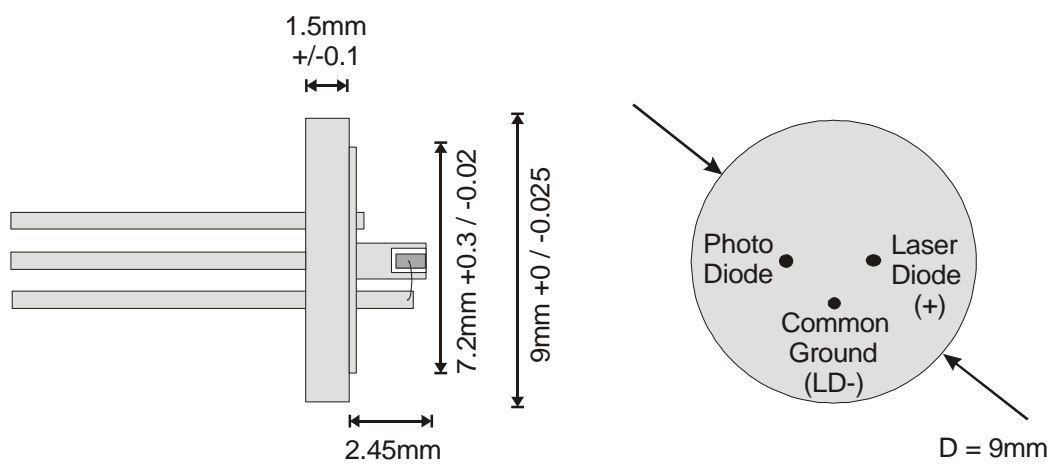
Model-No.: DFB-1872-003, DFB Diode Laser

Description: The DFB-1872-003 is a MOVPE grown GaInAsP/InP Distributed Feedback diode laser. The chips are mounted in 9mm TO-can. The diode laser operates spatially and longitudinally single mode.

Characteristics: The characteristics are measured at 25°C operation temperature.

Paramter	Symbol	Unit	Min.	typ.	max.
Center Wavelength	λ_c	nm	1867	1872	1877
Spectral Width	$\Delta\lambda$	MHz		5	10
Temperature Coefficient	$\Delta T/\Delta\lambda$	m/K		0.12	
Output Power	P_{opt}	mW		2	3
Slope Efficiency	η	mW/mA	0.06	0.075	0.9
Threshold Current	I_{th}	mA	35	40	45
Operation Current @ 3mW	I_{op}	mA		80	100
Chip Length	L_c	μm		600	
Emitter width	W_c	μm		2.8	
Beam Divergence (FWHM)	$\theta_{ }$	deg.		16	
Beam Divergence \perp (FWHM)	θ_{\perp}	deg.		30	
Polarzation				TE	
Mode Structure			fundamental transverse mode		

Laser Mount: 9mm TO-can without monitor diode



Side View of the Laser Mount

Rear View of the Laser Mount

Document: <http://data.sacher-laser.com/dbr/DFB1872003.pdf>
 Note: Specification are subject to change without further notice

